

High Purity SiC Powder



LG Innotek's high purity silicon carbide powder is specially synthesized to reduce impurities to extremely low level which can be used in manufacturing next generation power devices, LED, and equipment parts where any impurities can create problems.

PCG Series : For SiC Crystal Growth (6N Grade)

PCG series can be used in manufacturing semiconductor grade silicon carbide ingots used as the substrate materials for the next generation power devices and LED where any impurities can create problems. The particle size is typically controlled over 100 μm to meet the needs of silicon carbide crystal growth by PVT.

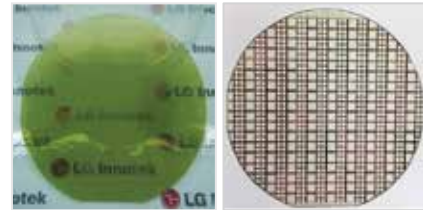
Properties	Unit	Spec.
Impurity	ppm	< 1.0
Particle Size (D_{50})	μm	230 \pm 30
Span (D_{90} / D_{10})	-	< 5.0
Total Nitrogen	ppm	< 200
Total Oxygen	ppm	< 200
Total Silicon	wt%	69~71
Total Carbon	wt%	29~31
Free Carbon	wt%	< 0.1
Free Silicon	wt%	< 0.01
Apparent Density	g/cm^3	> 1.7
Tapping Density	g/cm^3	> 1.9

PCG SiC Powder



SiC Wafer

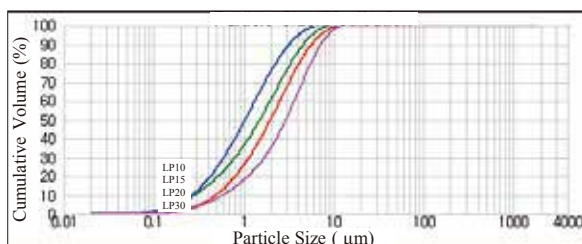
SiC Power Device



LP Series : For SiC Components

LP series are fine & high-purity silicon carbide powders to suit the material needs for high performance structural ceramic parts used in semiconductor and LED industries. The particle size is controlled below 3 μm for better sintering process conditions using high purity silicon carbide.

Properties	Unit	Spec.
Impurity (9 elements)	ppm	< 1.0
Particle Size (D_{50})	μm	1~3
Span (D_{90} / D_{10})	-	< 20
Free Carbon	ppm	< 1.0
Total Oxygen	ppm	< 1.0



LP SiC Powder



SiC Ring

SiC Susceptor

